

File View Edit Tools Window Help

Pending

Active

- L25: (6) (((select\$4 adj transistor) with (((Global main common))
- L26: (20) (((Global main common))
- L27: (26) 25 26
- L28: (1) 09/956212
- L30: (182712) short\$4 adj circuit\$4
- L31: (2853) (((Global main common)) | adj ((bl bitline bit adj line))
- L32: (52) 30 same 31
- L33: (37123) select\$4 adj (transistor device)
- L34: (12) 32 and 33
- L35: (263) 30 and 31
- L36: (83) 33 and 35
- L29: (27) 27 28

Failed

Saved

- (1) 09/948877
- (1738) "KONINKLIJKE PHILIPS".as.
- (0) 10/604406
- (1) 09/056212
- (1) 6620670.pn.
- (1) 09/653541
- (785087) (bl bitline bit adj line readline read adj line sense adj line column)
- (79745) (bl bitline bit adj line)
- (10789) select\$4 adj transistor

DBs: USPAT, US POPUB, EPO, JPO, DE PVENT, ISM, TTD

Default operator: OR

Highlight all hit terms initially

27 28

act 2003

U	I	Investor	Document	Issue	P	Title	Current	Current(XR)	Retrieval	S	C	P	Image	Doc	P
1		Onakado, Ta	US 8172397	200104	4	Non-volatile semiconductor memory device	257/321;257/315;							US 817239	P
2		Shiba, Kazuy	US 6038170	200002	2	Semiconductor integrated circuit device incl	365/185;257/E21.66							US 603817	P
3		Wang, Chan-j	US 5545585	199801	1	Method of making a dram circuit with fin sha	438/397;257/E21.01							US 554558	P
4		Hsu, Ching-Hs	US 2003005	200301	1	Nonvolatile semiconductor memory device h	365/185;							US 200300	P
5		Lee, Peter W.	US 6620682	200305	5	Set of three level concurrent word line bias	438/257;438/14;							US 662068	P
6		Parat, Krishn	US 2001002	200102	2	Novel flash integratad circuit and its method	438/259;438/257;							US 200100	P
7		Guo, Jyh-Chy	US 2001000	200102	2	Floating gate memory with substrate band-to	257/200;257/E28.30							US 200100	P
8		Lee, Yong-Ky	US 6583188	200301	1	Non-volatile semiconductor device with anti-	257/318;257/328							US 658318	P
9		Guo, Jyh-Chy	US 6352886	200202	2	Method of manufacturing floating gate mem	438/201;257/E29.30							US 635288	P
10		Parat, Krishn	US 6265282	200101	1	Method of fabrication of a novel flash integr	438/524;438/434;							US 626528	P

Ready